

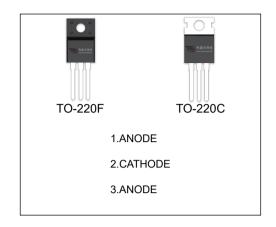
# MUR1040CT MURF1040CT SUPER FAST

### MAIN CHARACTERISTICS

Io	10A
V <sub>RRM</sub>	400 V
Tj	150 ℃
V <sub>F(typ)</sub>	1.1V (@Tj=125℃)

#### **FEATURES**

- Ultrafast 35ns Recovery Times
- High Voltage Capability to 400V
- Low Reverse Leakage Current



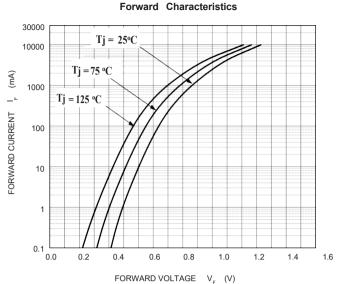
## MAXIMUM RATINGS ( T<sub>a</sub>=25℃ unless otherwise noted )

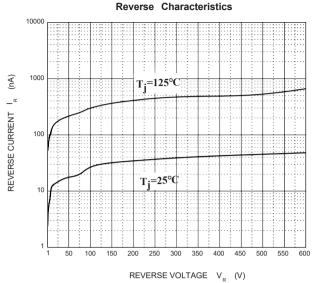
Symbol	Parameter	MU	MUR		
Symbol	Symbol		F1040CT	Unit	
V <sub>RRM</sub>	Peak repetitive reverse voltage				
V <sub>RWM</sub>	Working peak reverse voltage	4	400		
V <sub>R</sub>	DC blocking voltage				
V <sub>R(RMS)</sub>	RMS reverse voltage	2	280		
	Average rectified output current@ Per leg		5		
Io	Average rectified output current@ Total device	1	10		
1	Non-Repetitive peak forward surge current	70		А	
I <sub>FSM</sub>	8.3ms half sine wave				
P <sub>D</sub>	Power dissipation 2		W		
Roja	Thermal resistance from junction to ambient 62.5		2.5	°C/W	
T <sub>j</sub>	Operating Junction Temperature Range -55 ~ +150		+150	℃	
T <sub>stg</sub>	Storage Temperature Range -55 ~ +150		℃		

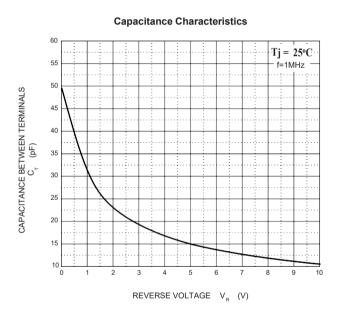
#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100uA		400			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =400V	Tj =25℃		0.2	1	uA
			Tj =125℃		1.0		uA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =5.0A	Tj =25℃		1.25	1.4	V
			Tj =125℃		1.1		V
Typical total capacitance	C <sub>tot</sub>	V <sub>R</sub> =4.0V,f=1MHz			16		pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5A, I <sub>R</sub> =1A,I <sub>rr</sub> =0.25A				35	ns









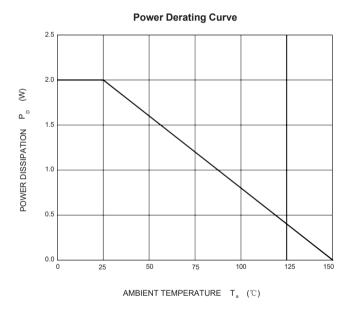


Diagram of circuit and Testing wave form of reverse recovery time

